



浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specification of products

产品名称：可控硅模块

产品型号：MFC200A1600VY01

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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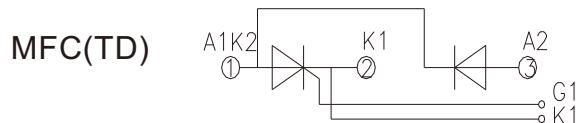
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^\circ C$	125			200	A
$I_{T(RMS)}$	RMS on-state current					314	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}$ tp=10ms $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 200V$ respectively	125		1600		V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			20	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=60\%V_{RRM}$	125			7.0	kA
I^2t	I^2t for fusing coordination					245	$A^2s * 10^3$
V_{TO}	Threshold voltage		125			0.8	V
r_T	On-state slope resistance					1.30	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=600A$	25			1.50	V
V_{FM}	Peak on-state voltage	$I_{FM}=600A$	25			1.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			1000	$V/\mu s$
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu s$ Repetitive	125			200	$A/\mu s$
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	30		180	mA
V_{GT}	Gate trigger voltage			0.8		2.5	V
I_H	Holding current			10		180	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.2	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.14	$^\circ C/W$
$R_{th(c-h)}$	Thermal resistance case to heat sink	Single side cooled per chip				0.08	$^\circ C/W$
V_{iso}	Isolation voltage	50Hz, R.M.S t=1min, I_{iso} :1mA(MAX)		3000			V
F_m	Terminal connection torque (M6)				5.0		$N\cdot m$
	Mounting torque (M6)				5.0		$N\cdot m$
T_{vj}	Junction temperature			-40		125	$^\circ C$
T_{stg}	Stored temperature			-40		125	$^\circ C$
W_t	Weight				370		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



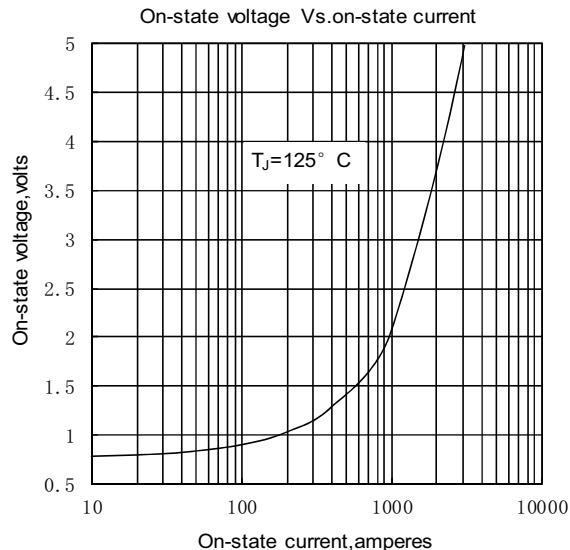


Fig.1

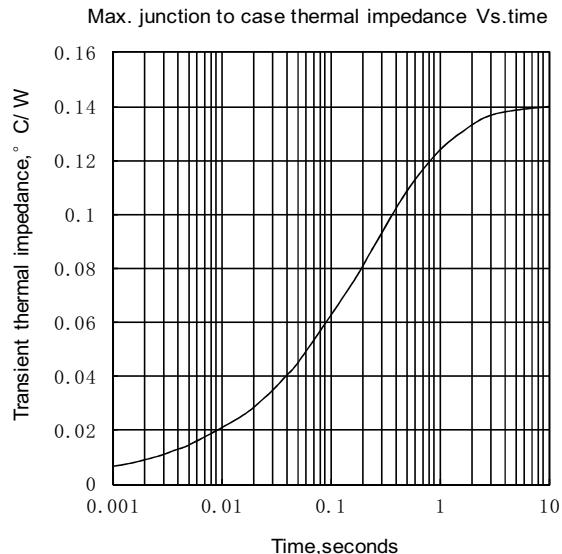


Fig.2

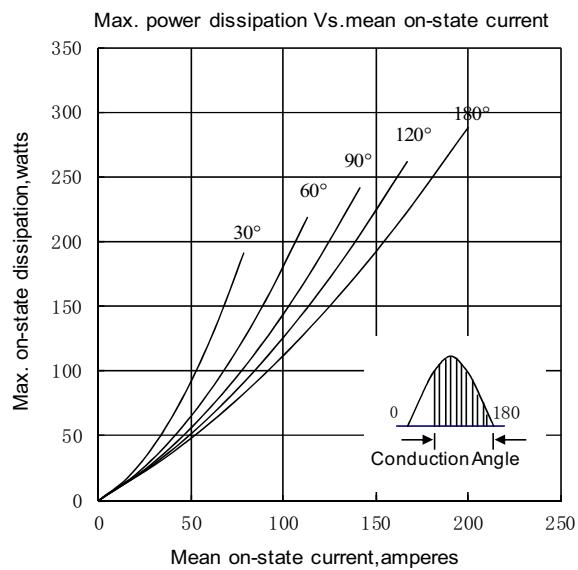


Fig.3

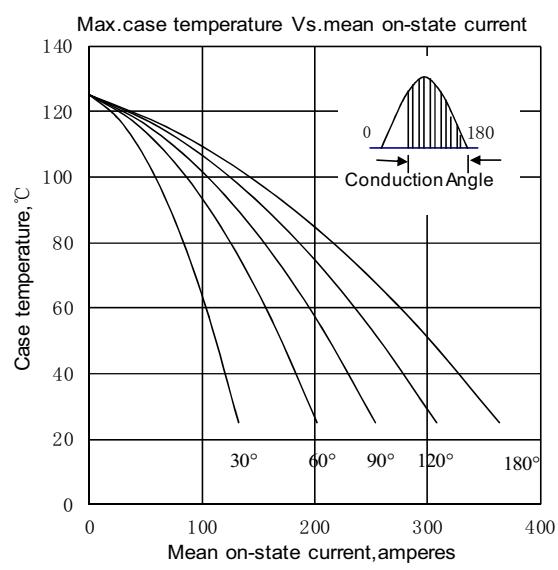


Fig.4

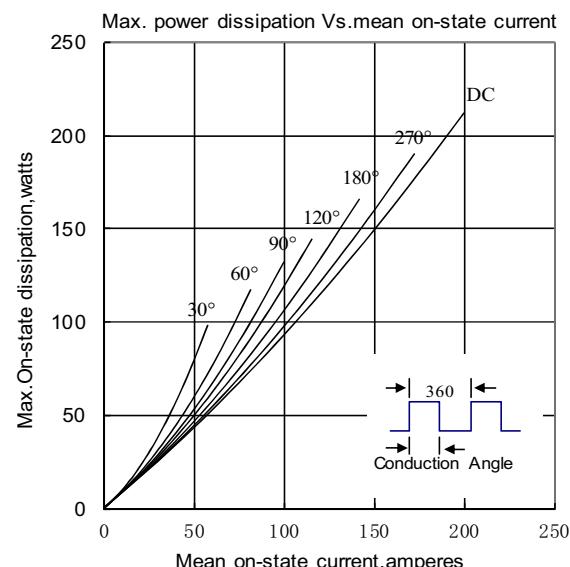


Fig.5

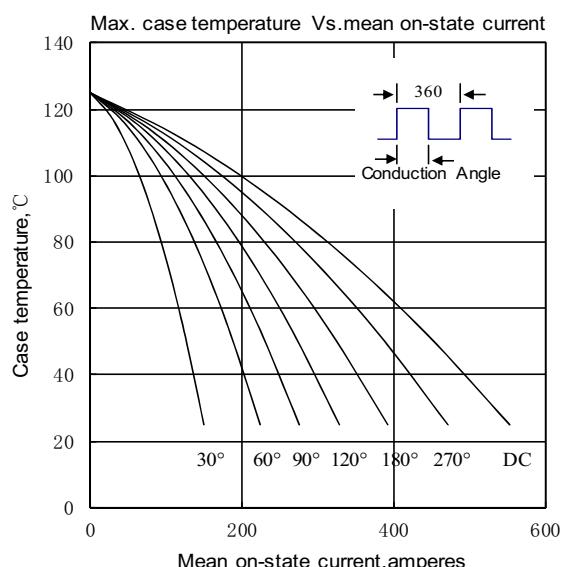


Fig.6

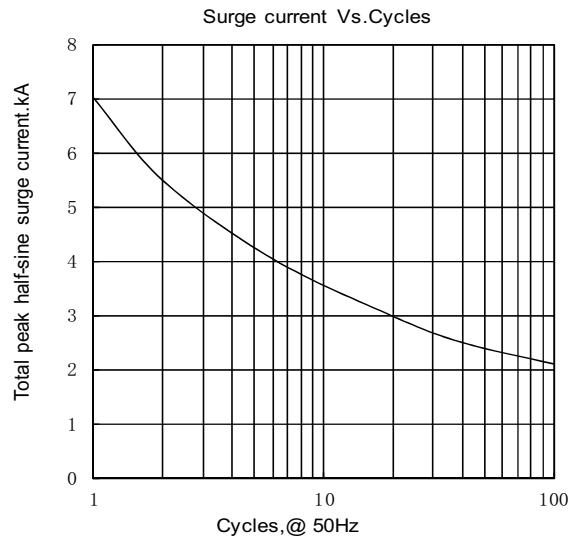


Fig.7

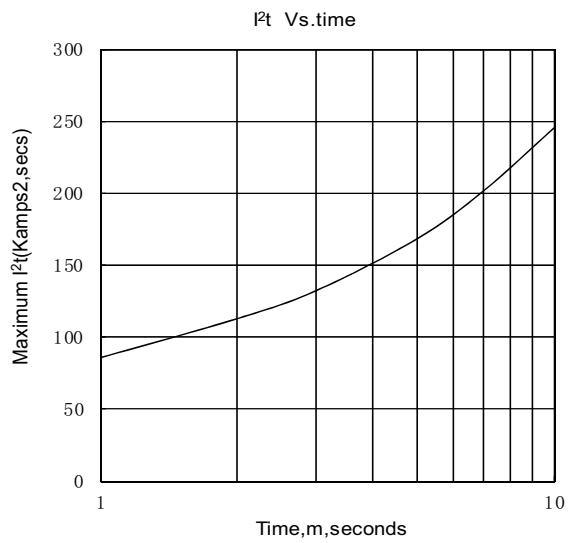


Fig.8

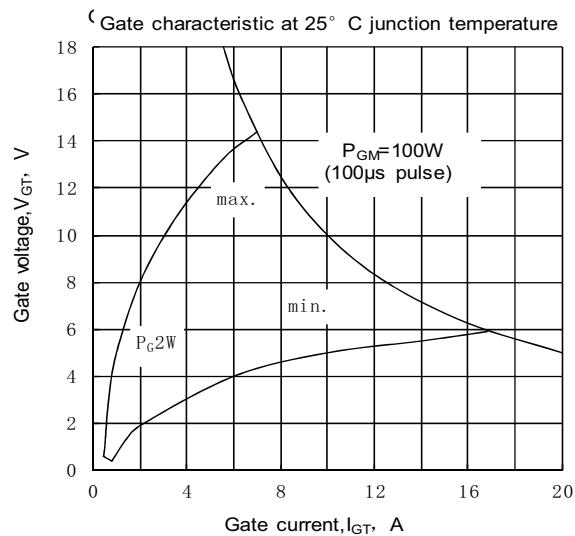


Fig.9

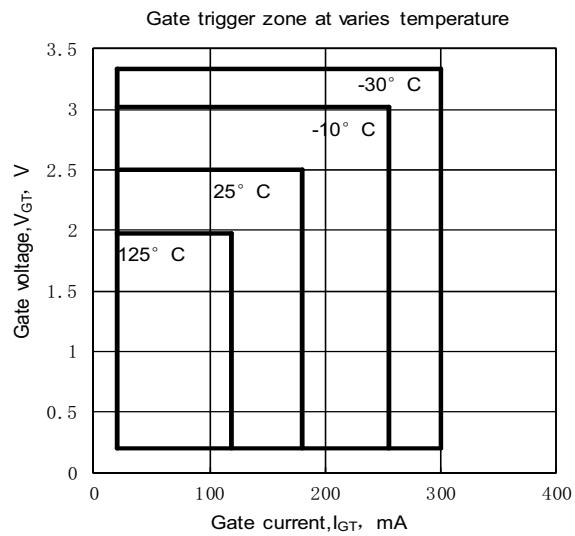


Fig.10

Outside Dimension

